Preparation and structural characterization of SnO$_2$ and GeO$_2$ methanol steam reforming thin film model catalysts by (HR)TEM

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Abstract
Structure, morphology and composition of different tin oxide and germanium oxide thin film catalysts for the methanol steam reforming (MSR) reaction have been studied by a combination of (High-resolution) Transmission Electron Microscopy, Selected Area Electron Diffraction, Dark-field imaging and Electron Energy-Loss Spectroscopy. Deposition of the thin films on NaCl(001) cleavage faces has been carried out by thermal evaporation of the respective SnO$_2$ and GeO$_2$ powders in varying oxygen partial pressures and at different substrate temperatures. Preparation of tin oxide films in high oxygen pressures (10$^4$ mbar) exclusively resulted in SnO phases, at and above 473 K substrate temperature epitaxial growth of SnO on NaCl(001) leads to well-ordered films. For lower oxygen partial pressures (10$^3$-10$^5$ mbar), mixtures of SnO and β-Sn are obtained. Well-ordered SnO$_2$ films, as verified by electron diffraction patterns and energy loss spectra, are only obtained after post-oxidation of SnO films at temperatures $T \geq 673$ K in 1 bar O$_2$. Preparation of GeO$_2$ films inevitably results in amorphous films with a composition close to GeO$_2$, which cannot be crystallized by annealing treatments in oxygen or hydrogen at temperatures comparable to SnO/SnO$_2$. Similarities and differences to neighbouring oxides relevant for selective MSR in the third group of the periodic system (In$_2$O$_3$, Ga$_2$O$_3$) are also discussed with the aim of cross-correlation in formation of nanomaterials, and ultimately, also catalytic properties.

Keywords: Electron Microscopy, Electron-Energy Loss Spectroscopy, SnO, Thin Films, Catalysis

1. Introduction
SnO$_2$ is one of the most extensively studied and best characterized oxides thanks to its outstanding chemical and electronic properties. A comprehensive review of all aspects especially of its surface and materials science has been given by Batzill et al.[1]. Recent important applications of SnO$_2$ range from solid state gas sensors (especially for reducing gases such as H$_2$, CO or H$_2$S) over transparent conductors to heterogeneous catalysis [1,2]. As these applications strongly depend on the structure and morphology of the SnO$_2$ samples, special attention has been paid to the development of reproducible preparation methods of a variety of SnO$_2$ samples, especially ordered thin films suitable for (high-resolution) transmission electron microscopy (HR(TEM)) characterization. These methods include sputtering, spray pyrolysis, electron-beam evaporation, chemical vapour deposition or rheotaxial growth and thermal oxidation, among others [3-7]. A concise discussion of different preparation techniques for thin films has been outlined by Sherveglieri et al.[8]. Regarding heterogeneous catalysis, the activity and selectivity of SnO$_2$ catalysts can be significantly improved by doping with other metals, such as Cu, Pd, Cr or Sb, but even pure SnO$_2$ itself is an active oxidation catalyst, especially in CO oxidation reactions. Since a Mars-van-Krevelen-type reaction mechanism is assumed to be prevalent, a central issue in oxidation catalysis of SnO$_2$ refers to its easy (surface) reducibility [1]. Most important, recent investigations indicate that pure SnO$_2$ exhibits a pronounced activity and/or selectivity in methanol steam...
reforming [9]. This behaviour places SnO$_2$ in line with other, previously studied oxides such as ZnO [10], Ga$_2$O$_3$ [11] or In$_2$O$_3$ [12]. The main feature of all these oxides is their role as supports and/or catalysts in methanol steam reforming, but, depending on the surface chemistry and redox properties, the desired selectivity to CO$_2$ varies. Pure In$_2$O$_3$ is highly CO$_2$-selective, both ZnO and Ga$_2$O$_3$ are not [11,13]. Partly this is also due to their activity in the reverse water-gas shift reaction [14,15]. From a chemical analogy argument, Sn$^{+4}$ and In$^{+3}$ represent isoelectronic species and therefore we may speculate about a potential functional analogy of their catalytic activity. The same holds for Ge$^{+4}$, Ga$^{+3}$ and Zn$^{+2}$, which renders an extension of the studies to the fourth main group of the periodic system useful. Contrary to SnO$_2$, structural information on GeO$_2$ thin films is scarce and mainly limited to the preparation of GeO$_2$ nanomaterials [16-18]. Catalytic information on GeO$_2$ is virtually non-existent, especially concerning methanol steam reforming.

In order to close the materials gap between surface studies especially on tin oxides, where a considerable amount of data already exists [1] and studies on “real world” powder catalysts, the thin film model concept will be exploited. From the structural point of view, thin films grown on well-ordered substrates are usually epitaxial or at least well-ordered, that is, structurally resembling single crystal studies conducted in UHV. At the same time, our thin film dedicated micro reactor setup allows correlation of the catalytic activity/selectivity measured on both thin film and powder samples [11,12]. The aim of the present contribution therefore is - in close correlation to similar studies on Ga$_2$O$_3$ and In$_2$O$_3$ [11-12] - to use NaCl(001) cleavage faces as substrates to eventually grow single-crystalline tin and germanium oxide films to present an easy and reproducible preparation pathway to different thin film model systems of tin and germanium oxides and subsequently their thorough structural characterization, prior to catalytic testing (see part B [19]). Adequate tools to fulfil this task are considered HRTEM, selected area electron diffraction (SAED) and electron energy-loss spectroscopy (EELS). In part B [19] the structural properties are linked to catalytic activity and selectivity in methanol steam reforming. Special attention will also be paid to the influence of deposition parameters (O$_2$ background pressure, substrate temperature) on film stoichiometry and morphology.

2. Experimental

All tin and germanium oxide films were prepared in a high-vacuum chamber operated at a base pressure of 10$^{-4}$ Pa. Film thicknesses (usually 25nm) were measured in-situ by a quartz crystal microbalance. SnO$_2$ and GeO$_2$ powders (Tin (IV) oxide, 99.99%, and Germanium (IV) oxide, 99.9999%, both Alfa Aesar) were thermally evaporated from tantalum crucibles onto vacuum-cleaved NaCl (001) surfaces at varying substrate temperatures (298 K-603 K) and O$_2$ background pressures (10$^{-2}$-10$^{-3}$ mbar). The films were floated and rinsed with distilled water, dried and finally mounted on gold grids for electron microscopy. Annealing and oxidative treatments (1 bar He or O$_2$ for 1 h at 473 K, respectively) were performed in a circulating batch reactor. The structure and morphology of these thin films in the as-deposited state and upon oxidative and annealing treatments were monitored by (High-resolution)-Transmission Electron Microscopy (HRTEM). The electron diffraction patterns were externally calibrated with respect to the (111), (200) and (220) Pd reflections of an as-deposited, untreated Pd/Ga$_2$O$_3$ catalyst. Overview TEM imaging and Selected Area Electron Diffraction (SAED) were carried out with a ZEISS EM10C microscope, high-resolution imaging, Electron Energy-Loss Spectroscopy (EELS), and Dark-Field imaging were performed using a JEOL 4000EX high resolution microscope operated at 400 kV and a JEOL 3000F FASTEM microscope operated at 300 kV and equipped with a GIF 2000 post-column electron energy-loss spectrometer. The film composition was checked by Energy-dispersive X-ray Analysis (EDXS), which only showed peaks due the evaporated elemental thin film constituents (Sn, Ge and O) and the gold grid (Au). Surface carbon impurities present on the films were removed by Ar-sputtering prior to TEM imaging. The purity of the substrate was ensured by freshly cleaving the NaCl(001) crystals immediately before deposition of the oxide.

3. Results and Discussion

3.1. SnO and SnO$_2$ thin films

3.1.1. Preparation of SnO thin film model catalysts

The structure of the SnO films after deposition in 10$^{-3}$ mbar Pa O$_2$ at low substrate temperatures (373 K) is shown in Figure 1. Although the film exhibits no pronounced contrast in bright-field TEM images, its regular grain-size structure is easily visible. The average size of the round-shaped grains is approximately 10 nm. The corresponding SAED pattern (shown as inset) represents an almost amorphous structure and shows a single blurred diffraction ring. Raising the substrate temperature to 473 K converts the film into a single crystalline phase, as revealed by the SAED pattern shown in Figure 2b. Four-fold split intense diffraction spots at 2.7Å, 1.9Å and 1.3Å correspond to the SnO (110), (200) and (220) lattice spacings of the tetragonal SnO phase (lattice constants a=3.79Å and c=4.84Å respectively [d$_{\text{SnO}}$ (110) = 2.686Å, d$_{\text{SnO}}$ (200) = 1.899Å, d$_{\text{SnO}}$ (220) = 1.343Å] [20]. As expected for the tetragonal phase, the (110)/(2-20) spots form an angle of 45° with the (200) diffraction spots. The corresponding bright-field TEM image (Figure 2a) exhibits much enhanced diffraction contrast and shows extended dark domains corresponding to differently oriented SnO grains. These observations are corroborated by additional high-
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Fig. 1: Overview bright-field TEM image of a SnO thin film after deposition at 373 K on NaCl(001) in 10\(^{-3}\) mbar O\(_2\). The SAED pattern is shown as an inset.

Resolution imaging, shown in Figure 3. The HRTEM image in Figure 3 reveals a complex arrangement of individual SnO grains each exhibiting lattice fringes of ~ 3.0Å, corresponding to the SnO (101) lattice spacings \(d_{\text{SnO}(101)}=2.989\text{Å}\) [20]. The inset Fast Fourier Transform pattern (i.e. the micro-diffraction pattern) evidences these extended SnO(101) lattice spacings by an ring at ~ 3.0Å, in agreement with the SAED patterns obtained from this sample. The FFT pattern also shows some reflections at ~ 2.7 Å spacing, corresponding to the SnO (110) lattice spacing.

Both electron diffraction and HRTEM therefore unambiguously confirm that after deposition at 473 K in 0.1 Pa O\(_2\) a single, well-ordered SnO phase is formed. Furthermore, the SAED pattern of Figure 2b suggests a preferential epitaxial growth of SnO on NaCl(001) in the relationship SnO[001]//NaCl[001] and SnO[011]//NaCl[011]. These observations agree well with previous studies of Choi et al. or Feng et al., where highly oriented tin oxide films (mostly tetragonal SnO\(_2\)) were successfully grown on single crystalline Al\(_2\)O\(_3\) substrates [2,21]. From dark-field experiments (shown in Figure 4) we also infer that the contrast variations are due to diffraction contrast of differently oriented SnO grains. The dark-field image was taken by using the SnO (200) diffraction spot. Consequently, grains giving rise to this diffraction spot appear bright in the dark-field image. All other differently oriented grains remain dark (see e.g. areas indicated by arrows in the lower left corner of the image).

A more complex scenario is present if the substrate temperature is raised to 573 K (Figure 5). The bright-field TEM image in Figure 5a shows a complete reconstruction of the SnO structure and extended Moire-fringes indicate overlapping lattice of differently oriented SnO grains. However, the SAED patterns (not shown) are identical to...
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Fig. 5: Overview bright-field TEM image of a SnO thin film after deposition at 573 K on NaCl(001) in \(10^{-7}\) mbar O\(_2\) (a) and a HRTEM image showing a small SnO\(_2\) region within the SnO film (b). The [001] zone axis orientation and structure of the SnO\(_2\) region is evidenced by the inset FFT pattern.

Fig. 6: Overview bright-field TEM image of a SnO thin film after deposition at 473 K on NaCl(001) in \(10^{-4}\) mbar O\(_2\) (a) and \(10^{-5}\) mbar O\(_2\) (b). The SAED patterns are shown as insets.

...the one shown in Figure 2b, indicating that most of the film remains SnO. Some small areas of the film have however almost fully oxidized to SnO\(_2\) as a result of the raising of the substrate temperature. The high-resolution image in Figure 5b shows such an area. All reflections in the FFT pattern fit with the tetragonal SnO\(_2\) structure imaged along the [001] zone axis orientation.

The effect of O\(_2\) background pressure variation at constant substrate temperature is highlighted in Figure 6. The left panel shows growth of SnO at 473 K in \(10^{-7}\) mbar O\(_2\), on the right panel the same situation in \(10^{-5}\) mbar O\(_2\) is outlined. In the TEM image of Figure 6a the former SnO structure formed after deposition at 473 K in \(10^{-7}\) mbar O\(_2\) is still prevailing, but additional round-shaped grains of about 20-30 nm size are also observed. The SAED pattern (inset) still shows strong diffraction spots of the tetragonal SnO phase, but also additional Debye-Scherrer-type diffraction rings. A detailed analysis reveals the presence of a second metallic β-Sn phase, with strong reflections at 2.9Å and 2.8Å, corresponding to the β-Sn(200) and β-Sn(101) fringes [22]. It is worth noting, that these sphere-like structure corresponds to the first stages of oxide film preparation by rheotaxial growth and thermal oxidation [7,8], where metallic tin is deposited to form large droplets and subsequently oxidized to result in an oxide film with a high surface-to-volume ratio. These features are even more pronounced if the deposition is carried out with less O\(_2\) (Figure 6b). At \(10^{-5}\) mbar O\(_2\) background pressure the film structure does not resemble SnO, but rather shows very large sphere-like aggregates (up to 50 nm in size). The SAED patterns still show SnO, but the intensity of the β-Sn phase increased considerably.

The issue of influence of O\(_2\) background pressure on phase formation has also been addressed by Jimenez et al. upon SnO and SnO\(_2\) deposition on MgO and SiO\(_2\) [23]. In agreement with the present studies, heating of SnO\(_2\) and post-exposition to 0.1 Torr (~13 Pa) O\(_2\) for 300 s resulted only in SnO stoichiometry. Complete oxidation to SnO\(_2\) was only obtained after exposure to an oxygen plasma at 300 K. In general, SnO thin films are mostly prepared via oxidation of Sn layers [24] or spray pyrolysis [25]. However, the above-outlined preparation method is unique since it yields reproducible and well-ordered SnO films at low substrate temperatures.

3.1.1. Preparation of SnO\(_2\) thin film model catalysts

The question how to reproducibly prepare SnO\(_2\) thin films is intimately connected with the ability to carry out deposition of tin oxides at oxygen background pressures higher than \(10^{-5}\) mbar. Usually, e.g. for Ga\(_2\)O\(_3\) or In\(_2\)O\(_3\), an oxygen background pressure of \(10^{-4}\) mbar is sufficient to fully oxidize the respective thin films during deposition. Deposition of tin oxides is different since both of the oxides, SnO\(_2\) and SnO\(_2\), are thermodynamically stable oxides and deposition in \(10^{-3}\) mbar O\(_2\) only leads to SnO phases. Higher oxygen background pressures, even if they are needed for SnO\(_2\) deposition, are basically excluded since the deposition rate decreases drastically for very high oxy
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Fig. 7: Overview bright-field TEM image of a SnO thin film after deposition at 573 K on NaCl(001) in 10⁻³ mbar O₂ after post-oxidation at 673 K in 1 bar O₂ for 1h.

Fig. 8: High-resolution electron micrograph of the thin film shown in Figure 7. The inset SAED pattern evidences the tetragonal SnO₂ crystal structure, a faint diffuse ring corresponding to the SnO (101) spacing can also be made out. The arrows indicate examples of widespread defects (stacking faults) present in the film.

gen background pressures due to oxidative inhibition of the formation of volatile gas phase species. Hence, the only preparation pathway to SnO₂ thin films, if the deposition is carried out by thermal evaporation of SnO₂ is via formation of SnO and adequate post-oxidation procedures.

Figure 7 highlights the structure of a previous SnO film prepared at 473 K in 10⁻³ mbar oxygen background pressure and post-oxidized at 673 K in 1 bar O₂. The overview TEM image reveals a coarse grain structure similar to the original SnO film and exhibits strong diffraction contrast. However, the corresponding HRTEM images and SAED patterns indicate formation of SnO₂. Figure 8 shows a high-resolution TEM image with extended SnOₓ(110) lattice fringes of 3.30Å spacing, corroborating the SAED analysis. The inset ED ring pattern mainly shows rings corresponding to the SnO₂ structure (at 3.4Å, 2.6Å, 2.4Å and 1.8Å, corresponding to the (110), (101), (200) and (211) reflections of the tetragonal SnO₂ structure (a=4.73Å, c=3.18Å; dᵧtheor(110)=3.347Å; dᵧtheor(101)=2.643Å; dᵧtheor(200)=2.369Å; dᵧtheor(211)=1.764Å) [26]. It is worth noting, that SnO₂ appears to be at least partially ordered, as judged from the elongated diffraction spots overlapping with the diffraction rings. A single diffuse ring at 3.0Å is present, arising from a very small amount of SnO. The arrows in the HRTEM image indicate the widespread defective (mainly stacking faults) structure of the SnO₂ film.

Additional information on the formation of different tin oxide species is provided by EELS. Figure 9 shows an overview of the Sn M₄,5 and O-K edges of SnO films after deposition at 473 K in 10⁻³ mbar O₂ (middle), after post-oxidation at 673 K (top) and after reduction at 573 K in 1 bar hydrogen (bottom). The interaction of the tin oxides with hydrogen is discussed in part B, but for the sake of clarity, the EELS spectrum is included in this figure. Due to the different structural environments in SnO and SnO₂ (tetrahedral vs. trigonal oxygen coordination in the first coordination shell) [27] the electron-energy near-edge structure of the Sn M₄,5 and O-K-edges is a reliable tool to distinguish between the different types of tin oxides. The topmost spectrum is typical for SnO₂, with a wider splitting of the peaks in the region 530-550 eV and the more pronounced multiple scattering resonances at higher energy.

Fig. 9: EELS spectra (Sn-M₄,5 edge at 485 eV and O-K edge at 532 eV) of differently prepared tin oxide thin films (top: SnO correspond- ing to the thin film shown in Figure 7; middle: SnO corre- sponding to the film shown in Figure 2; bottom: SnO thin film after reduction in H₂ at 573 K (1 bar, 1h)). The two oxide phases can be discerned by the splitting of the fine structure after 530 eV as well as the elevated peak at 550-560 eV in SnO₂ (indicated by *) [27].
losses (around 575 eV). In contrast, the middle spectrum shows two peaks of almost equal intensity with a narrower splitting and a slightly less pronounced ELNES around 570-575 eV. These differences are basically due to the different coordination of oxygen in both tin oxides [27]. The bottom spectrum, corresponding to β-Sn according to the SAED patterns, only shows a broad edge typical for a delayed Sn M₁,₃ edge [27].

3.2. GeO₂ thin films

The preparation of ordered, single-phase GeO₂ thin films is hampered by the polymorphism of GeO₂, that is, it exists not only a hexagonal α-quartz-type and a tetragonal rutile-type structure but also a glassy amorphous phase depending on pressure, temperature and preparation conditions. Concerning the preparation of thin films using NaCl as growth templates, the solubility of the different polymorphs in water is most crucial. Whereas α-quartz-type GeO₂ is slightly soluble in water, rutile-type GeO₂ is insoluble [28]. Depending on which phase forms, floating the thin films in water therefore might pose problems, whereas α-quartz-type GeO₂ films are almost uniquely prepared by oxidative treatments of Ge [29]. However, as discussed below, we succeeded in preparing self-supporting GeO₂ films, which are not affected by the floating procedure. Generally, GeO₂ samples are almost uniquely prepared by oxidative treatments of Ge films or powders [18,30].

For GeO₂ we followed a similar strategy as for Sn and SnO₂ and tried to assess structure, composition and influence of deposition parameters. Figure 10 shows a bright-field overview TEM image of a GeO₂ thin film prepared at 300 K and 10⁻⁴ mbar O₂ background pressure. Both the image and the SAED pattern (inset) indicate the presence of an amorphous germanium oxide phase. It is worth to note, that neither raising the substrate temperature to 623 K nor post-oxidation treatments up to 673 K lead to the formation of single crystalline phases and only low contrast amorphous structures are obtained. Recent studies have shown that thin films prepared by evaporation of GeO₂ are usually sub-stoichiometric and can only be crystallized by post-annealing at very high temperatures [31,32]. Our observations agree well with studies of Ardyanin et al. on the structure and photoluminescence properties of e-beam evaporated GeO₂ films. GeO₂ was evaporated in UHV at 10⁻⁸ Torr (with pressure increase to 3x10⁻⁶ Torr during deposition) at 373 K on silicon substrates and only amorphous GeO₂ films were obtained (film thickness: 200 nm). Only after annealing at 773 K, disproportion of GeO₂ into crystalline Ge metal and amorphous GeO₂ was observed [32]. As the method of choice to gain information on the composition of the amorphous GeO₂ films, EELS spectra of the as-deposited thin film, after oxidation at 673 K and after reduction in H₂ at 673 K were collected. This will also ensure a direct correlation to the properties of SnOₓ films. Figure 11 highlights a set of O K-edges and Ge L_{2,3}-edges of the films after the above mentioned treatments. In short, these edges are typical of α-quartz-type GeO₂ [33] and no substantial differences between the spectra can be detected. Most important, the spectra allow the determination of the film stoichiometry by quantification of the oxygen-to-germanium ratios. For the as-deposited film and the oxidized sample, ratios of O : Ge = 66 at% : 34 at% and 67 at % : 33 at%, respectively, have been obtained. This indicates that already after deposition the film stoichiometry is close to GeO₂. For the reduced sample, this ratio shifts to O : Ge = 58 at% : 42 at%, indicating that the overall film stoichiometry changes towards GeO₂. We therefore assume that the films are close to a GeO₂ stoichiometry in the as-deposited state and annealing treatments (also in hydrogen and oxygen) up to 673 K, which
are typically used for catalyst regeneration treatments, are not sufficient to induce a complete reduction of GeO\textsubscript{2}, disproportion of GeO\textsubscript{3} or the formation of any crystalline phase (metallic or oxidic).

4. Conclusions

We successfully demonstrated reproducible preparation pathways to thin film model catalysts of SnO, SnO\textsubscript{2} and GeO\textsubscript{2} by simple thermal evaporation of SnO\textsubscript{2} and GeO\textsubscript{2} in different oxygen environments and, for SnO\textsubscript{2}, by post-oxidation of the resulting films at 673 K. Generally, some differences and similarities to the previously studied neighbouring oxides (In\textsubscript{2}O\textsubscript{3}, Ga\textsubscript{2}O\textsubscript{3}) in the third group of the periodic system are notable [11,12]. From the structural point of view, SnO/SnO\textsubscript{2} more closely resembles In\textsubscript{2}O\textsubscript{3} thin films in terms of crystallinity and epitaxial growth. Both materials show a strong dependence of the film structure and morphology on the substrate temperature, although formation of nano-materials, such as octahedrons or pyramidal-shaped particles as obtained for In\textsubscript{2}O\textsubscript{3}, has never been observed. On the contrary, GeO\textsubscript{2} films resemble Ga\textsubscript{2}O\textsubscript{3} structures, at least at low substrate temperatures. For both materials, amorphous structures are usually observed, even after oxidative and annealing treatments at temperatures as high as 673 K. As for SnO/SnO\textsubscript{2}, no nano-architectures have been observed for GeO\textsubscript{2} even at high substrate temperatures (623 K). This behaviour might be interpreted in terms of the presence of different growth species during oxide deposition and the resulting altered wetting properties on NaCl(001). For Ga\textsubscript{2}O\textsubscript{3} and In\textsubscript{2}O\textsubscript{3}, these growth species were basically associated with sub-stoichiometric oxides (e.g. Ga\textsubscript{2}O or In\textsubscript{2}O) with a high mobility on NaCl(001) at high substrate temperatures. Therefore, the formation of the sphere-like aggregates for Ga\textsubscript{2}O\textsubscript{3} and pyramidal-shaped particles for In\textsubscript{2}O\textsubscript{3} is the result of efficient transport processes preceding the oxidation of the volatile sub-stoichiometric oxides and their re-oxidation towards ordered aggregates (apart from crystallographic matching of In\textsubscript{2}O\textsubscript{3} and NaCl). For SnO\textsubscript{2}, we might interpret the growth species as SnO and/or Sn metal, as confirmed by the SAED patterns of films prepared at different oxygen partial pressures. The highest oxygen partial pressures that can be used in our HV chamber during deposition (10\textsuperscript{-3} mbar) are sufficient to convert Sn metal into SnO\textsubscript{2}, but no further oxidation to SnO\textsubscript{3} can be achieved. The same probably holds for GeO\textsubscript{2}, but since only amorphous films are obtained, a thorough structural characterization by TEM, apart from EELS, is excluded. In any case, both oxides are promising candidates as supports for small Pd catalyst particles. Hence, bimetallic single phases of Pd-Sn and Pd-Ge might be prepared by reduction in hydrogen and catalytically characterized in methanol steam reforming, in close correlation to Pd supported on ZnO, Ga\textsubscript{2}O\textsubscript{3} and In\textsubscript{2}O\textsubscript{3}.

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